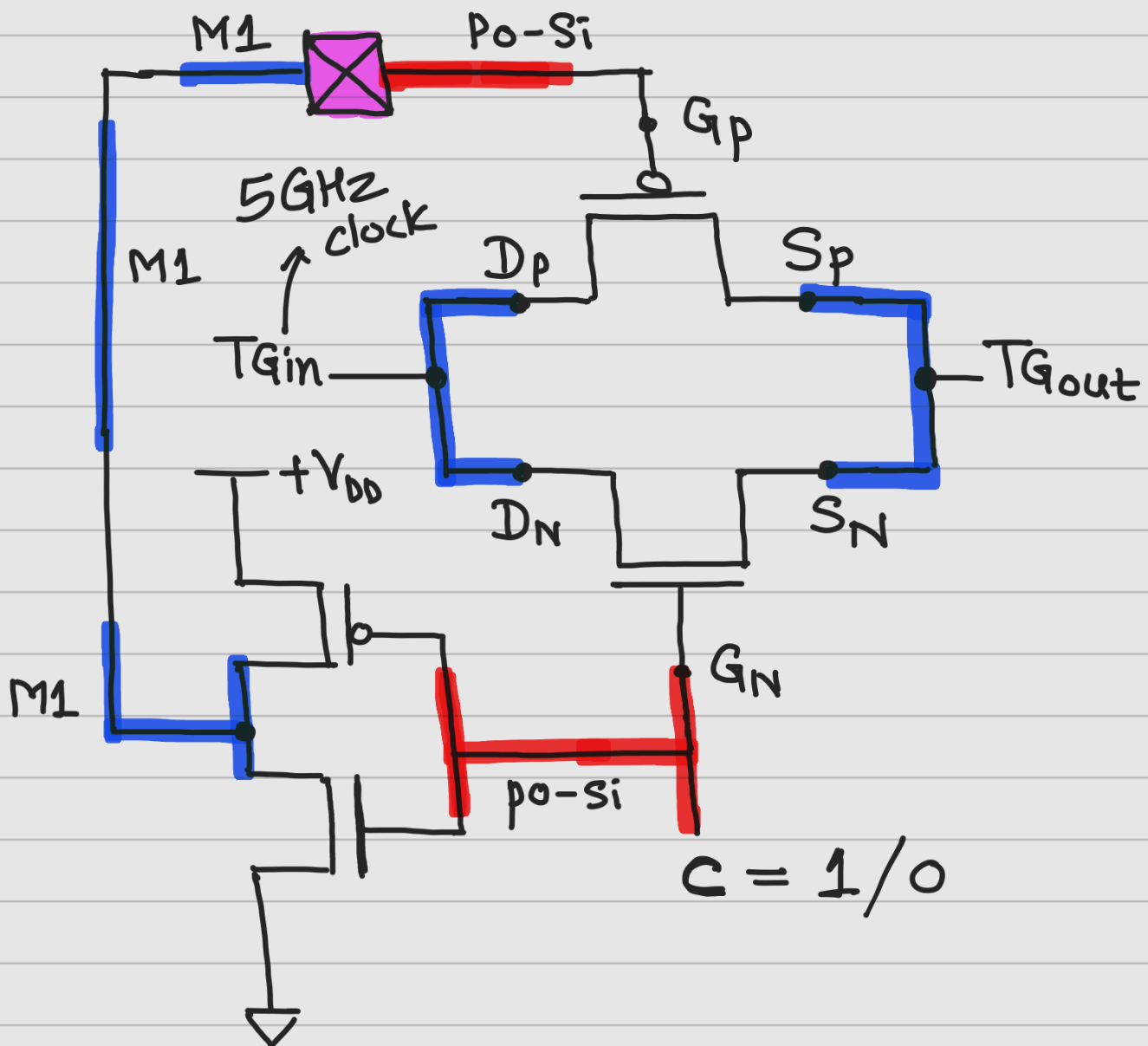


MOSFET-LEVEL SCHEMATIC OF TG



$$\begin{aligned} \underline{\text{PMOS:}} \quad \frac{W_p}{L_p} &= \left(\frac{500}{100} \right) \text{nm} = 5 = p \\ \underline{\text{NMOS:}} \quad \frac{W_n}{L_n} &= \left(\frac{500}{100} \right) \text{nm} = 5 = n \end{aligned} \quad \left. \vphantom{\frac{W_p}{L_p}} \right\} \frac{p}{n} = 1$$

■ Metal-1 Layer (M1)

■ Polysilicon Layer (po-si)

⊗ Metal-1 To Polysilicon contact closed s/w

For $C = 1$, $T_{Gout} = T_{Gin}$ (S-1, S-0)
 $C = 0$, $T_{Gout} \neq T_{Gin}$ (open s/w)